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A. Wilson

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>OW</i>	AA	2002/0052084	05/02/2002	Fitzgerald	438	282	05/02/2002
	AB						
	AC						
	AD						
	AE						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AF						
	AG						
	AH						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
<i>OW</i>	AI	"Channel width dependence of mobility in Ge channel modulation-doped structures," Irisawa et al. <i>Jpn. J. Appl. Phys.</i> April 2001. Vol. 40.
<i>OW</i>	AJ	"Thermal stability of Ge channel modulation doped structures," Irisawa et al. <i>Journal of Crystal Growth</i> . 2001. Vol. 227-228. *
<i>OW</i>	AK	"Hall mobility enhancement caused by annealing of $\text{Si}_{0.2}\text{Ge}_{0.8}/\text{Si}_{0.7}\text{Ge}_{0.3}/\text{Si}(001)$ p-type modulation-doped heterostructures," Myronov et al. <i>Applied Physics Letters</i> . May 2002. Vol. 80, No. 19.
<i>OW</i>	AL	"Quantum mechanical modeling of the charge distribution in a $\text{Si}/\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ P-Channel MOSFET," Hargrove et al. <i>Proceedings of the 1994 IEEE International Electron Devices Meeting</i> , San Francisco, CA. December 1994.
<i>OW</i>	AM	"Characteristics and device design of Sub-100 nm strained Si N- and PMOSFETs," Rim et al. <i>Symposium on VLSI Technology Digest of Technical Papers</i> . 2002. *
<i>OW</i>	AN	"Enhanced performance of strained-Si MOSFETs on CMP SiGe Virtual Substrate," Sugii et al. <i>International Electron Devices Meeting 2001. IEDM. Technical Digest</i> . *
<i>OW</i>	AO	"SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation," Cheng et al. <i>IEEE International SOI Conference</i> . Durango, CO. October 2001.
<i>OW</i>	AP	"Ultrahigh room-temperature hole hall and effective mobility in $\text{Si}_{0.3}\text{Ge}_{0.7}/\text{Ge}/\text{Si}_{0.3}\text{Ge}_{0.7}$ heterostructures," Irisawa et al. <i>Applied Physics Letters</i> . July 2002. Vol. 81, No. 5.

EXAMINER

DATE CONSIDERED

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Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

* No month cited.